

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16501FT

Low-Voltage 18-Bit Universal Bus Transceiver with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16501FT is a high performance CMOS 18-bit universal bus transceiver. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

Data flow in each direction is controlled by output-enable (OEAB and Oeba), latch-enable (LEAB and LEBA), and clock (CKAB and CKBA) inputs.

For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CKAB is held at a high or low logic level. If LEAB is low, the A bus data is stored in the latch/flip-flop on the low-to-high transition of CKAB.

Data flow for B to A is similar to that of A to B but uses OEBA, LEBA, and CKBA.

When the OE input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

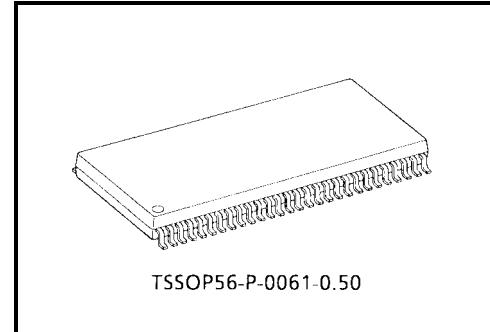
All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- High-speed operation: $t_{pd} = 2.9$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
 - : $t_{pd} = 3.5$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
 - : $t_{pd} = 7.0$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
 - : $I_{OH}/I_{OL} = \pm 18$ mA (min) ($V_{CC} = 2.3$ V)
 - : $I_{OH}/I_{OL} = \pm 6$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: ± 300 mA
- ESD performance: Machine model $> \pm 200$ V
 - : Human body model $> \pm 2000$ V
- Package: TSSOP (thin shrink small outline package)
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Note 1: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.



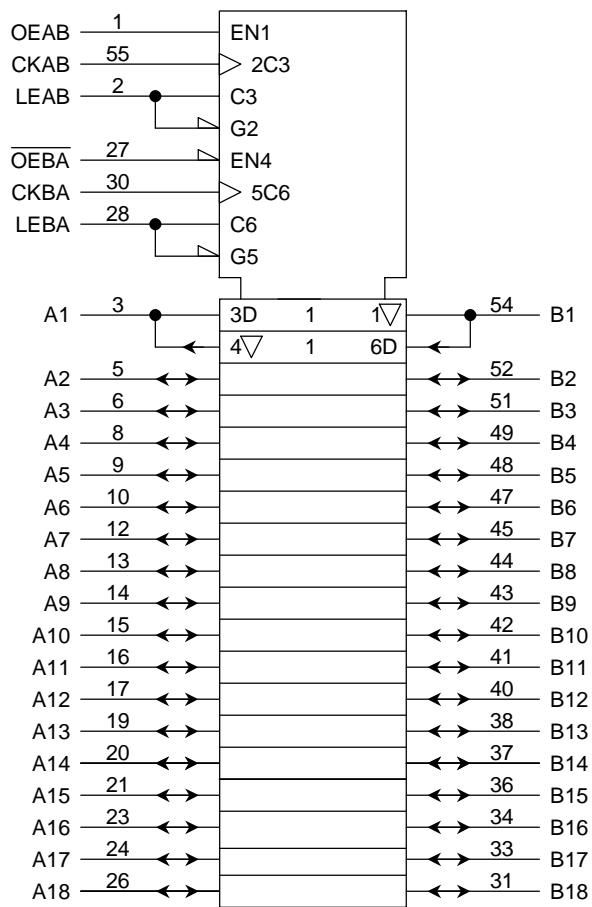
TSSOP56-P-0061-0.50

Weight: 0.25 g (typ.)

Pin Assignment (top view)

OEAB	1	
LEAB	2	
A1	3	
GND	4	
A2	5	
A3	6	
V _{CC}	7	
A4	8	
A5	9	
A6	10	
GND	11	
A7	12	
A8	13	
A9	14	
A10	15	
A11	16	
A12	17	
GND	18	
A13	19	
A14	20	
A15	21	
V _{CC}	22	
A16	23	
A17	24	
GND	25	
A18	26	
OEBA	27	
LEBA	28	
	56	GND
	55	CKAB
	54	B1
	53	GND
	52	B2
	51	B3
	50	V _{CC}
	49	B4
	48	B5
	47	B6
	46	GND
	45	B7
	44	B8
	43	B9
	42	B10
	41	B11
	40	B12
	39	GND
	38	B13
	37	B14
	36	B15
	35	V _{CC}
	34	B16
	33	B17
	32	GND
	31	B18
	30	CKBA
	29	GND

IEC Logic Symbol



Truth Table (A bus → B bus)

Inputs				Outputs B
OEAB	LEAB	CKAB	A	
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↑	L	L
H	L	↑	H	H
H	L	H	X	B0 (Note 2)
H	L	L	X	B0 (Note 2)

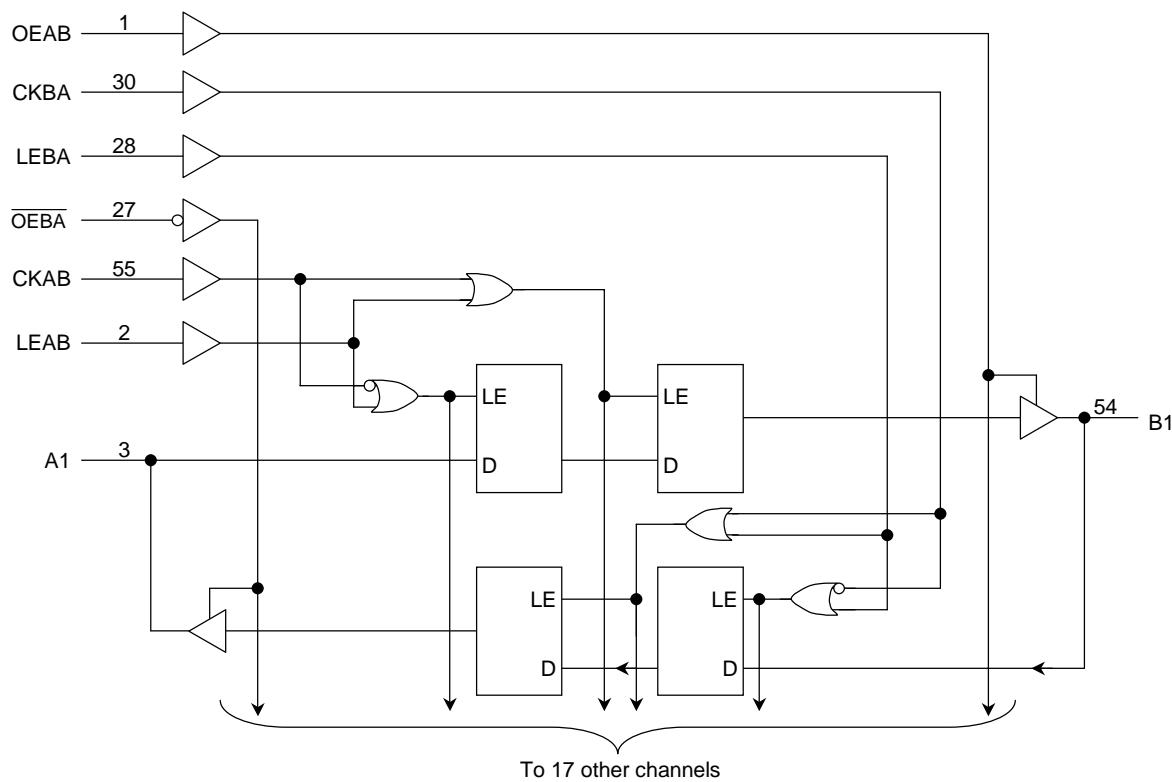
Note 2: Output level before the indicated steady-state input conditions were established, provided that CKAB was low or high before LEAB went low.

Truth Table (B bus → A bus)

Inputs				Outputs A
OEBA	LEBA	CKBA	B	
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H
L	L	H	X	A0 (Note 2)
L	L	L	X	A0 (Note 2)

Note 2: Output level before the indicated steady-state input conditions were established, provided that CKBA was low or high before LEBA went low.

System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	-0.5 to 4.6	V
DC input voltage (OEAB, \overline{OEBA} , LEAB, LEBA, CKAB, CKBA)	V_{IN}	-0.5 to 4.6	V
DC bus I/O voltage	$V_{I/O}$	-0.5 to 4.6 (Note 3)	V
		-0.5 to $V_{CC} + 0.5$ (Note 4)	
Input diode current	I_{IK}	-50	mA
Output diode current	I_{OK}	± 50 (Note 5)	mA
DC output current	I_{OUT}	± 50	mA
Power dissipation	P_D	400	mW
DC V_{CC} /ground current per supply pin	I_{CC}/I_{GND}	± 100	mA
Storage temperature	T_{stg}	-65 to 150	°C

Note 3: OFF state

Note 4: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 5: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 6)	
Input voltage (OEAB, \overline{OEBA} , LEAB, LEBA, CKAB, CKBA)	V_{IN}	-0.3 to 3.6	V
Bus I/O voltage	$V_{I/O}$	0 to 3.6 (Note 7)	V
		0 to V_{CC} (Note 8)	
Output current	I_{OH}/I_{OL}	± 24 (Note 9)	mA
		± 18 (Note 10)	
		± 6 (Note 11)	
Operating temperature	T_{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 12)	ns/V

Note 6: Data retention only

Note 7: OFF state

Note 8: High or low state

Note 9: $V_{CC} = 3.0$ to 3.6 V

Note 10: $V_{CC} = 2.3$ to 2.7 V

Note 11: $V_{CC} = 1.8$ V

Note 12: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V

Electrical Characteristics**DC Characteristics (Ta = -40 to 85°C, 2.7 V < V_{CC} ≤ 3.6 V)**

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	H-level		—	2.7 to 3.6					
	L-level	V _{IL}	—	2.7 to 3.6	—	0.8	—		
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	—	V	
				I _{OH} = -12 mA	2.7	2.2	—		
				I _{OH} = -18 mA	3.0	2.4	—		
				I _{OH} = -24 mA	3.0	2.2	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2		
				I _{OL} = 12 mA	2.7	—	0.4		
				I _{OL} = 18 mA	3.0	—	0.4		
				I _{OL} = 24 mA	3.0	—	0.55		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.7 to 3.6	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	—	20.0	μA	
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	—	750		

DC Characteristics (Ta = -40 to 85°C, 2.3 V ≤ V_{CC} ≤ 2.7 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	H-level		—	2.3 to 2.7	1.6	—			
	L-level	V _{IL}	—	2.3 to 2.7	—	0.7			
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	—	V	
				I _{OH} = -6 mA	2.3	2.0	—		
				I _{OH} = -12 mA	2.3	1.8	—		
				I _{OH} = -18 mA	2.3	1.7	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3 to 2.7	—	0.2		
				I _{OL} = 12 mA	2.3	—	0.4		
				I _{OL} = 18 mA	2.3	—	0.6		
				I _{OL} = 24 mA	2.3 to 2.7	—	0.55		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.3 to 2.7	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3 to 2.7	—	20.0	μA	

DC Characteristics ($T_a = -40$ to 85°C , $1.8 \text{ V} \leq V_{CC} < 2.3 \text{ V}$)

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit	
Input voltage	H-level	V_{IH}	—		1.8 to 2.3	$0.7 \times V_{CC}$	—	V	
	L-level	V_{IL}	—		1.8 to 2.3	—	$0.2 \times V_{CC}$		
Output voltage	H-level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	1.8	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -6 \text{ mA}$	1.8	1.4	—		
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	1.8	—	0.2		
				$I_{OL} = 6 \text{ mA}$	1.8	—	0.3		
Input leakage current		I_{IN}	$V_{IN} = 0$ to 3.6 V		1.8	—	± 5.0	μA	
3-state output OFF state current		I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		1.8	—	± 10.0	μA	
Power-off leakage current		I_{OFF}	$V_{IN}, V_{OUT} = 0$ to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC}$ or GND		1.8	—	20.0	μA	
			$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8	—	± 20.0		

AC Characteristics (Ta = -40 to 85°C, input: tr = tf = 2.0 ns, CL = 30 pF, RL = 500 Ω)

Characteristics	Symbol	Test Condition	VCC (V)	Min	Max	Unit
Maximum clock frequency	f _{max}	Figure 1, Figure 3	1.8	100	—	MHz
			2.5 ± 0.2	200	—	
			3.3 ± 0.3	250	—	
Propagation delay time (An, Bn-Bn, An)	t _{pLH}	Figure 1, Figure 2	1.8	1.5	7.0	ns
			2.5 ± 0.2	0.8	3.5	
	t _{pHL}		3.3 ± 0.3	0.6	2.9	
Propagation delay time (CKAB, CLKBA-Bn, An)	t _{pLH}	Figure 1, Figure 3	1.8	1.5	8.8	ns
			2.5 ± 0.2	0.8	4.4	
	t _{pHL}		3.3 ± 0.3	0.6	3.5	
Propagation delay time (LEAB, LEBA-Bn, An)	t _{pLH}	Figure 1, Figure 4	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	4.9	
	t _{pHL}		3.3 ± 0.3	0.6	3.8	
Output enable time (OEAB, OEBA-Bn, An)	t _{pZL}	Figure 1, Figure 5, Figure 6	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	4.9	
	t _{pZH}		3.3 ± 0.3	0.6	3.8	
Output disable time (OEAB, OEBA-Bn, An)	t _{pLZ}	Figure 1, Figure 5, Figure 6	1.8	1.5	7.6	ns
			2.5 ± 0.2	0.8	4.2	
	t _{pHZ}		3.3 ± 0.3	0.6	3.7	
Minimum pulse width	t _W (H) t _W (L)	Figure 1, Figure 3, Figure 4	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
	t _W (L)		3.3 ± 0.3	1.5	—	
Minimum set-up time	t _s	Figure 1, Figure 3, Figure 4	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum hold time	t _h	Figure 1, Figure 3, Figure 4	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output to output skew	tosLH tosHL	(Note 13)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For CL = 50 pF, add approximately 300 ps to the AC maximum specification.

Note 13: Parameter guaranteed by design.

$$(tosLH = |t_{pLHm} - t_{pLHn}|, tosHL = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics(Ta = 25°C, input: t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition		Typ.	Unit
		V _{CC} (V)			
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 1.8 V, V _{IL} = 0 V	(Note 14)	1.8	0.25
		V _{IH} = 2.5 V, V _{IL} = 0 V	(Note 14)	2.5	0.6
		V _{IH} = 3.3 V, V _{IL} = 0 V	(Note 14)	3.3	0.8
Quiet output minimum dynamic V _{OL}	V _{OLV}	V _{IH} = 1.8 V, V _{IL} = 0 V	(Note 14)	1.8	-0.25
		V _{IH} = 2.5 V, V _{IL} = 0 V	(Note 14)	2.5	-0.6
		V _{IH} = 3.3 V, V _{IL} = 0 V	(Note 14)	3.3	-0.8
Quiet output minimum dynamic V _{OH}	V _{OHV}	V _{IH} = 1.8 V, V _{IL} = 0 V	(Note 14)	1.8	1.5
		V _{IH} = 2.5 V, V _{IL} = 0 V	(Note 14)	2.5	1.9
		V _{IH} = 3.3 V, V _{IL} = 0 V	(Note 14)	3.3	2.2

Note 14: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		Typ.	Unit
		V _{CC} (V)			
Input capacitance	C _{IN}	—	—	1.8, 2.5, 3.3	pF
Bus I/O capacitance	C _{I/O}	—	—	1.8, 2.5, 3.3	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note 15)	1.8, 2.5, 3.3	pF

Note 15: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/18 \text{ (per bit)}$$

AC Test Circuit

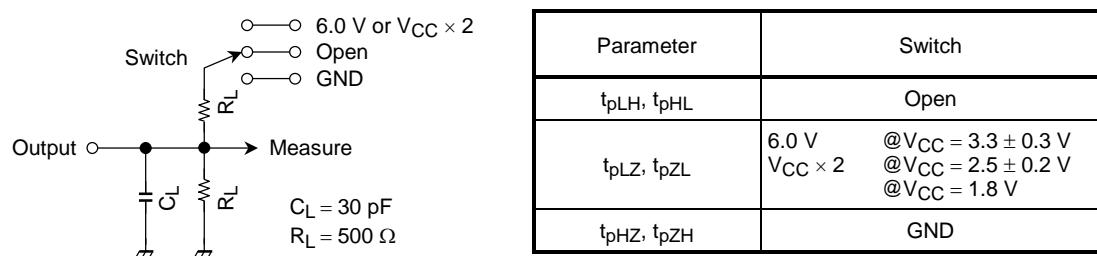
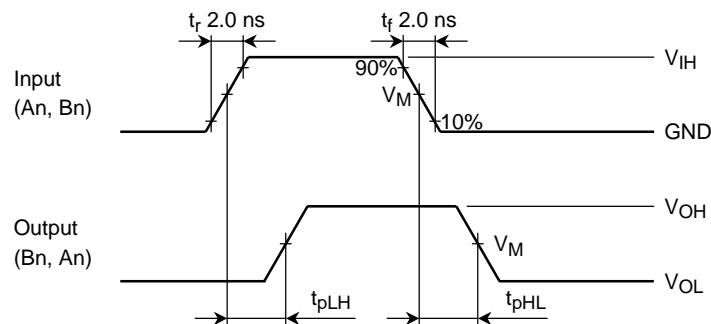
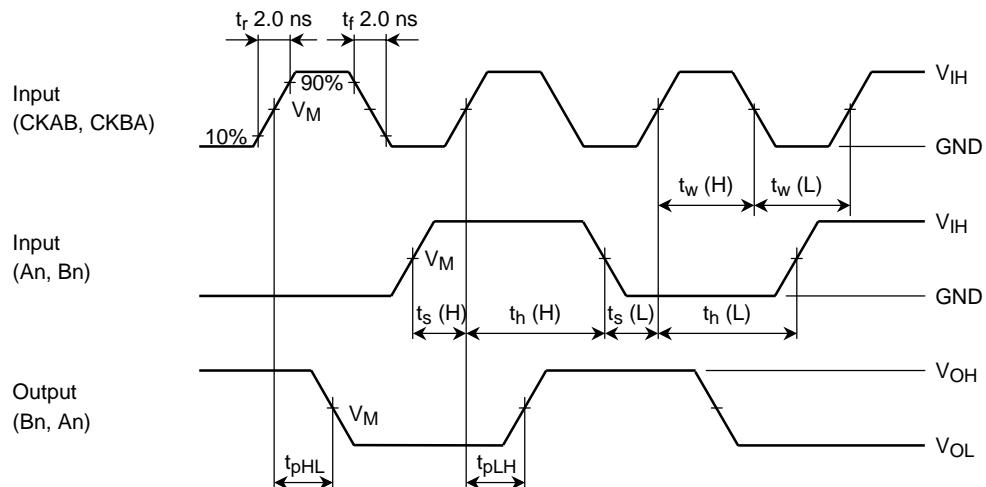
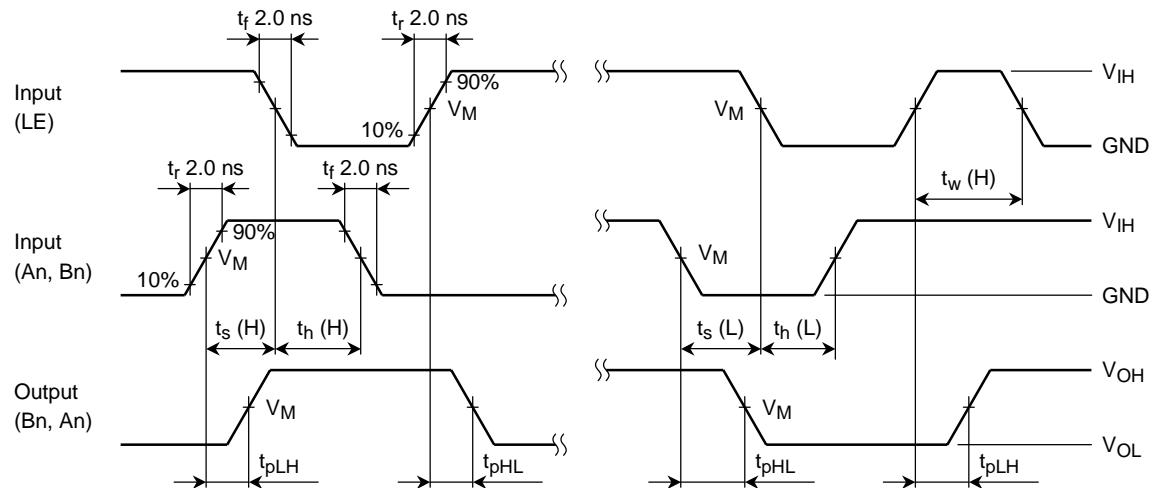
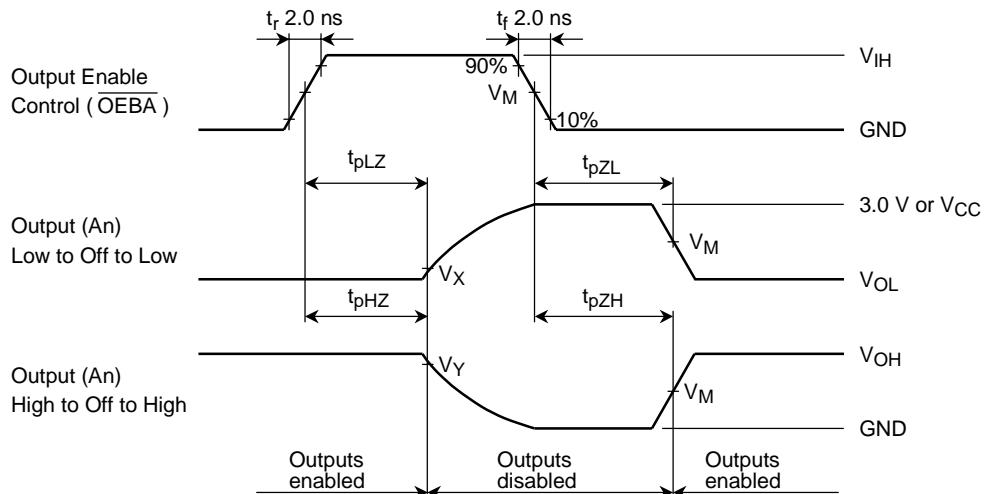


Figure 1

AC Waveform

Figure 2 t_{pLH}, t_{pHL} Figure 3 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

**Figure 4** t_{pLH} , t_{pHL} , t_w , t_s , t_h **Figure 5** t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

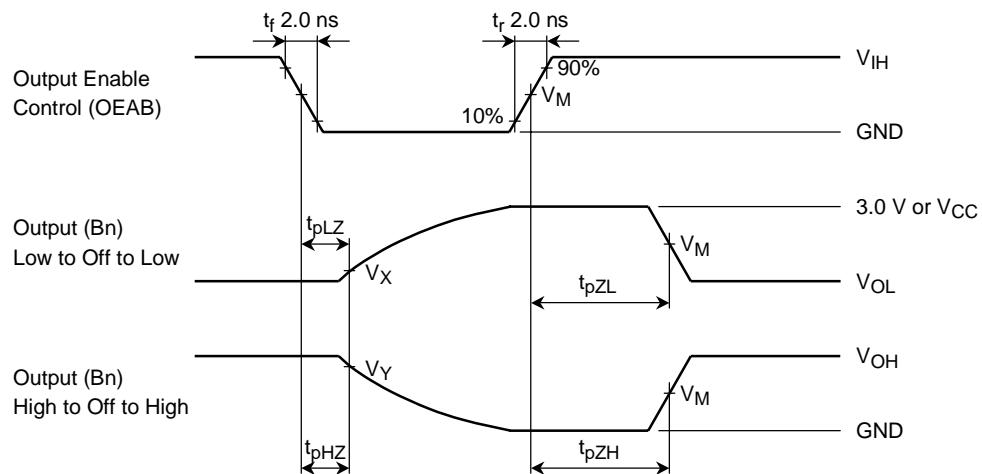


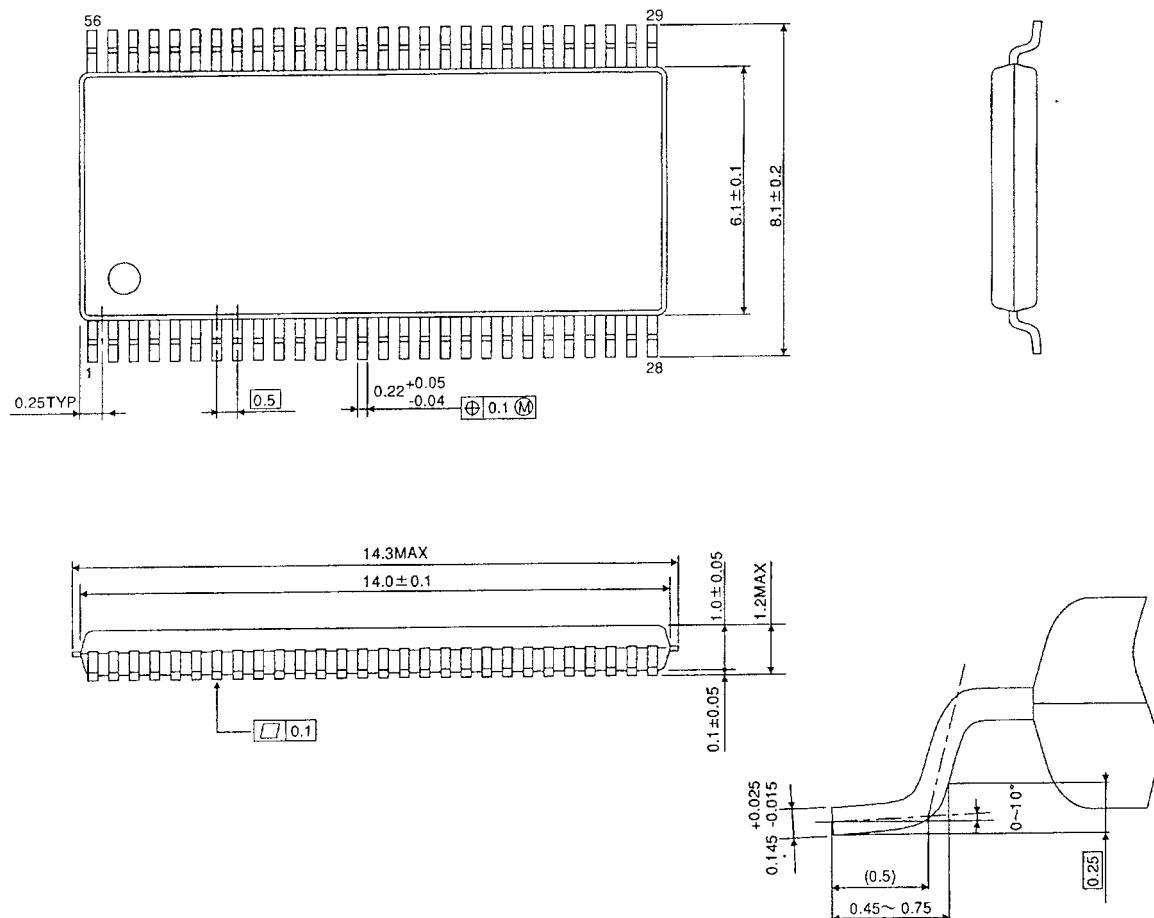
Figure 6 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V_{CC}		
	$3.3 \pm 0.3 \text{ V}$	$2.5 \pm 0.2 \text{ V}$	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3 \text{ V}$	$V_{OL} + 0.15 \text{ V}$	$V_{OL} + 0.15 \text{ V}$
V_Y	$V_{OH} - 0.3 \text{ V}$	$V_{OH} - 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$

Package Dimensions

TSSOP56-P-0061-0.50

Unit : mm



Weight: 0.25 g (typ.)

RESTRICTIONS ON PRODUCT USE

000707EBA

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